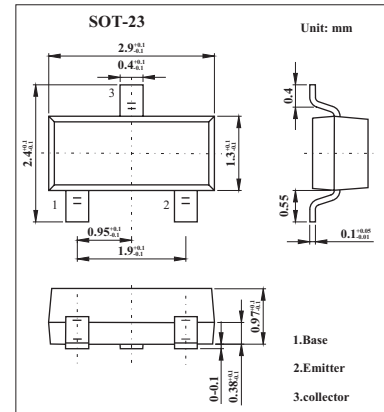


High Voltage Transistor

BSS63R

■ Features

- SOT23 PNP silicon planar

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	-110	V
Collector-emitter voltage	V_{CEO}	-100	V
Emitter-base voltage	V_{EBO}	-6	V
Continuous collector current	I_C	-100	mA
Power dissipation	P_{tot}	330	mW
Operating and storage temperature range	T_j, T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CB0}$	$I_C = -10\mu\text{A}$	-110			V
Collector-emitter breakdown voltage *	$V_{(BR)CEO}$	$I_C = -100\mu\text{A}$	-100			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu\text{A}$	-6			V
Collector-base cut-off current	I_{CBO}	$V_{CB} = -90\text{V}$ $V_{CB} = -90\text{V}, T_a = 150^\circ\text{C}$			-100 -50	nA μA
Emitter-base current	I_{EBO}	$V_{EB} = -6\text{V}$			-200	nA
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -25\text{mA}, I_B = -2.5\text{mA}$			-250	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -25\text{mA}, I_B = -2.5\text{mA}$			-900	V
DC current gain	h_{FE}	$I_C = -10\text{mA}, V_{CE} = -1\text{V}$ $I_C = -25\text{mA}, V_{CE} = -1\text{V}$	30 30			
Transitional frequency	f_T	$I_C = 25\text{mA}, V_{CE} = -5\text{V}, f = 35\text{MHz}$	50	85		MHz
Output capacitance	C_{obo}	$V_{CB} = -10\text{V}, f = 1\text{MHz}$		3		pF

* Pulse test: $t_p = 300\mu\text{s}; d \leq 0.02$.

■ Marking

Marking	T6
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